AT65R260IP/AT65R260IF/AT65R260IL

650V Super Junction Power MOSFET

Features

- Low drain-source on-resistance:$R_{DS(ON)}$=0.23Ω(typ)
- Easy to control gate switching
- Enhancement mode: V_{th} = 2.0 to 4.0V
- 100% avalanche tested
- RoHS compliant

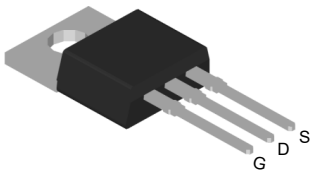
Key Performance Parameters

Parameter	Value	Unit
V_{DS} @ $T_{j,max}$	650	V
$R_{DS(ON),max}$	260	mΩ
I_D	15	A
$Q_{g,typ}$	27	nC
I_{DM}	45	A

Applications

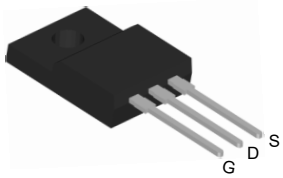
- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)
- Charger,Lighting

TO-220 Top View



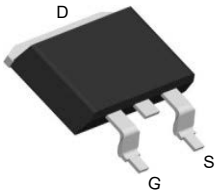
AT65R260IP

TO-220F Top View

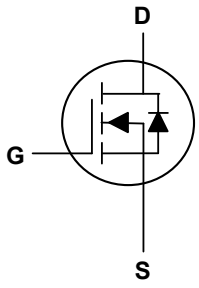


AT65R260IF

TO-263 Top View



AT65R260IL



Absolute Maximum Ratings(T_C=25℃, unless otherwise noted)

Parameter	Symbol	TO-220/TO-263	TO-220F	Unit
Drain-Source Voltage	V_{DS}	650		V
Gate-Source Voltage	V_{GS}	±30		V
Continuous Drain Current[1]	I_D	15		A
Pulsed Drain Current[2]	I_{DM}	45		A
Single Pulse Avalanche Energy[4]	EAS	290		mJ
Avalanche Current	I_{AS}	2.4		A
Repetitive Avalanche energy,t_{AR} limited by T_{Jmax}	E_{AR}	0.44		mJ
MOSFET dv/dt ruggedness, V_{DS} = 0...400V	dv/dt	50		V/ns
Reverse diode dv/dt[3] V_{DS}=0...400V, I_{SD}≤I_D		50		
Total Power Dissipation （T_C=25℃）	P_D	100	31	W
Storage Temperature Range	T_{STG}	-55 to 150		℃
Operating Junction Temperature Range	T_J	-55 to 150		℃

Thermal Characteristics

Parameter	Symbol	TO-220/TO-263	TO-220F	Unit
Thermal Resistance Junction-Ambient	$R_{\theta JA}$	62	80	℃/W
Thermal Resistance Junction-Case	$R_{\theta JC}$	1.6	4	℃/W

Electrical Characteristics (T_J=25℃, unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V , I_D=250uA	650	---	---	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}=10V , I_D=7.5A	---	230	260	mΩ
Gate Threshold Voltage	$V_{GS(th)}$	V_{GS}=V_{DS} , I_D =250uA	2.0	---	4.0	V
Drain-Source Leakage Current	I_{DSS}	V_{DS}=650V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=650V, V_{GS}=0V, T_J=150℃	---	---	100	
Gate-Source Leakage Current	I_{GSS}	V_{GS}=±30V , V_{DS}=0V	---	---	±100	nA
Gate Resistance	R_G	f = 1.0MHz, open drain	---	12	---	Ω
Total Gate Charge	Q_g	V_{DD}=400V , V_{GS}=10V , I_D=15A	---	27	---	nC
Gate-Source Charge	Q_{gs}		---	5.5	---	
Gate-Drain Charge	Q_{gd}		---	10.5	---	
Turn-On Delay Time	$T_{d(on)}$	V_{DD}=400V , V_{GS}=10V , R_G=25Ω, I_D=15A	---	25	---	ns
Rise Time	T_r		---	65	---	
Turn-Off Delay Time	$T_{d(off)}$		---	105	---	
Fall Time	T_f		---	50	---	
Input Capacitance	C_{iss}	V_{DS}=100V , V_{GS}=0V , f=1MHz	---	1170	---	pF
Output Capacitance	C_{oss}		---	51	---	
Reverse Transfer Capacitance	C_{rss}		---	7	---	

Drain-Source Diode Characteristics

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Continuous Source Current	I_S	T_C=25℃	---	---	15	A
Pulsed Source Current	I_{SM}		---	---	45	A
Diode Forward Voltage	V_{SD}	V_G=0V , I_S=15A ,T_J=25℃	---	0.9	1.2	V
Reverse Recovery Time	t_{rr}	V_R=400V, I_F=15 A, di_F/dt=100A/μs	---	410	---	ns
Reverse Recovery Charge	Q_{rr}		---	4	---	uC
Peak Reverse Recovery Current	I_{rrm}		---	20	---	A

Note:

1. Limited by $T_{j,max.}$ Maximum Duty Cycle D = 0.50
2. Pulse width t_p limited by $T_{j,max}$
3. Identical low side and high side switch with identical R_G
4. V_{DD}=50V,R_G=25Ω,I_{AS}=2.4A

Typical Characteristics

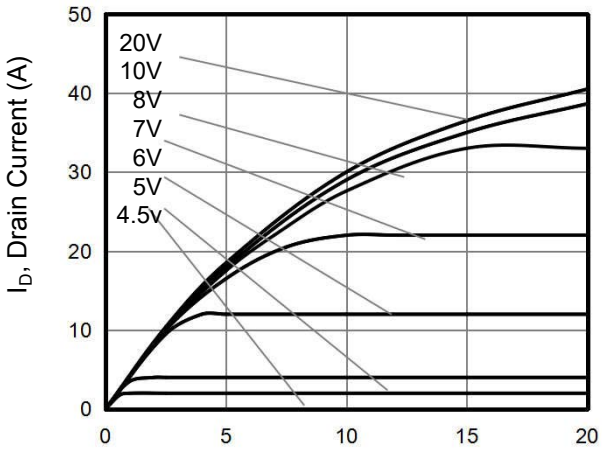


Figure 1. Output Characteristics

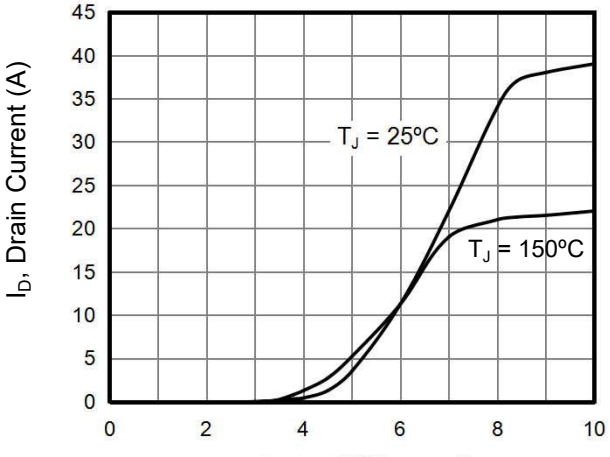


Figure 2. Transfer Characteristics

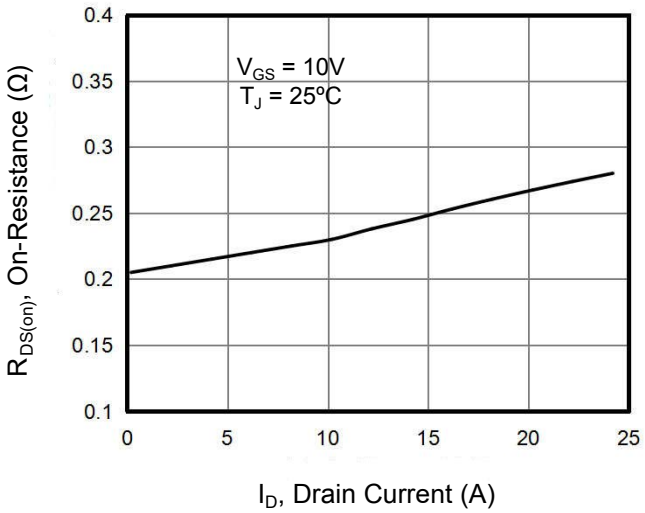


Figure 3. On-Resistance vs. Drain Current

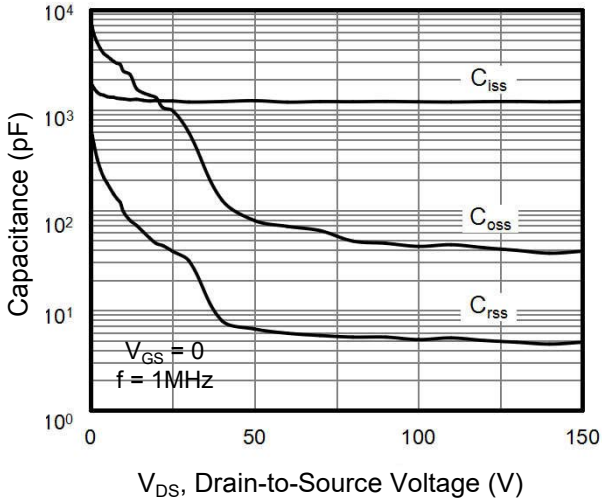


Figure 4. Capacitance

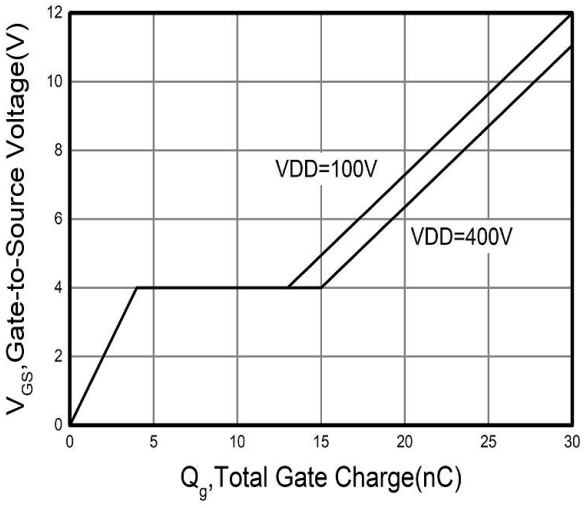


Figure 5. Gate Charge

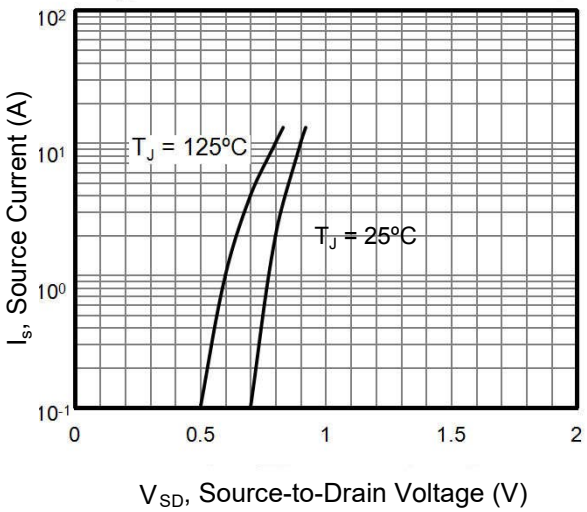


Figure 6. Body Diode Forward Voltage

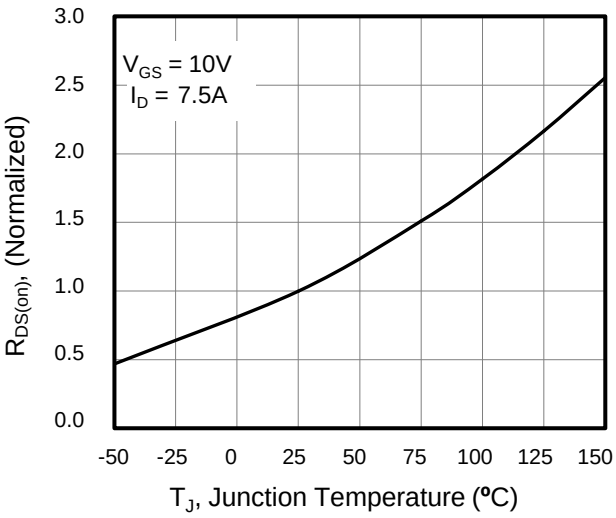


Figure 7. On-Resistance vs. Junction Temperature

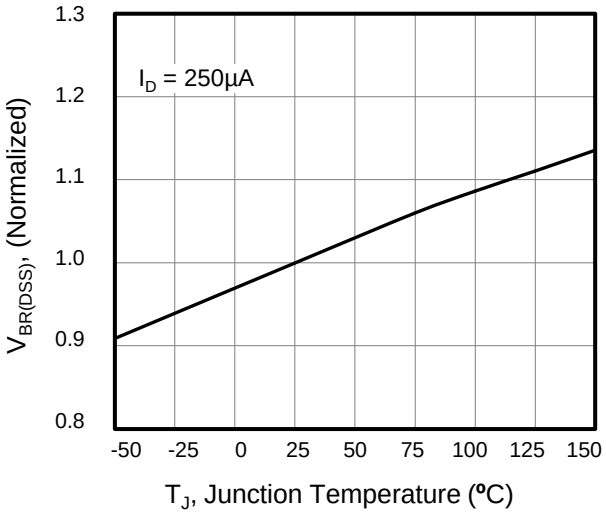


Figure 8. Breakdown voltage vs. Junction Temperature

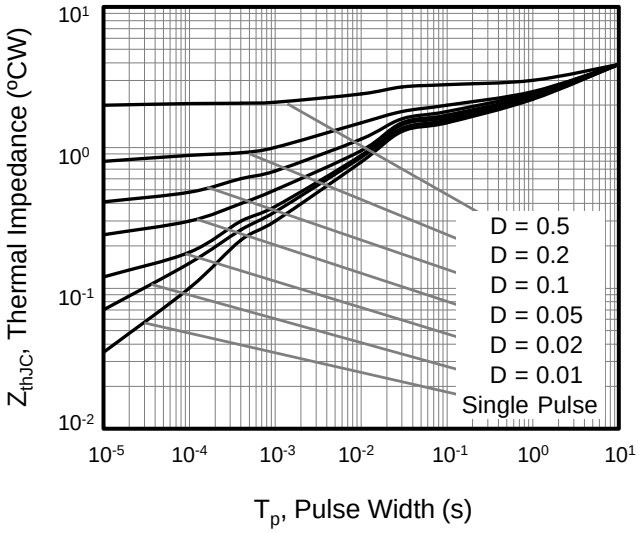


Figure 9. Transient Thermal Impedance TO-220F

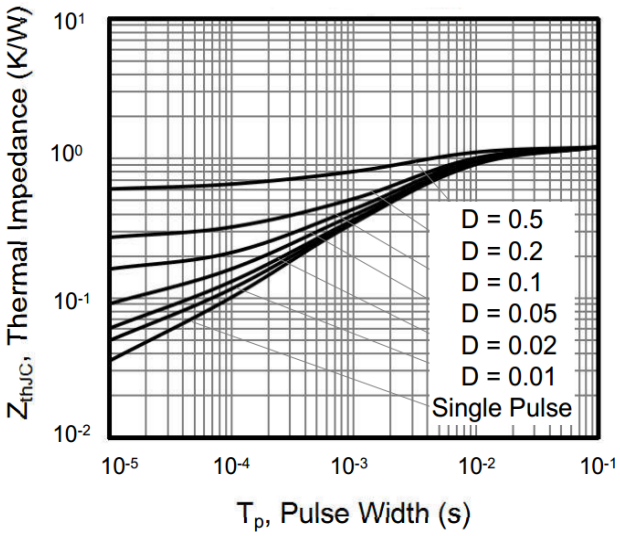
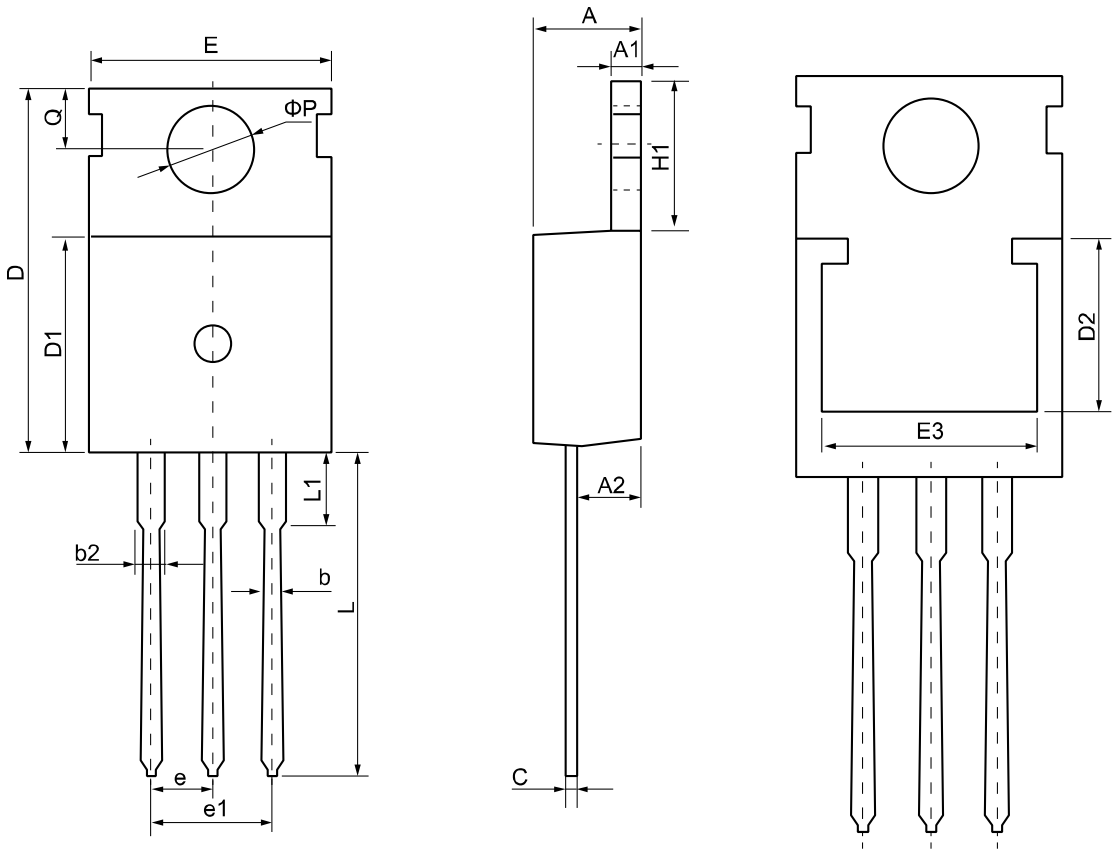


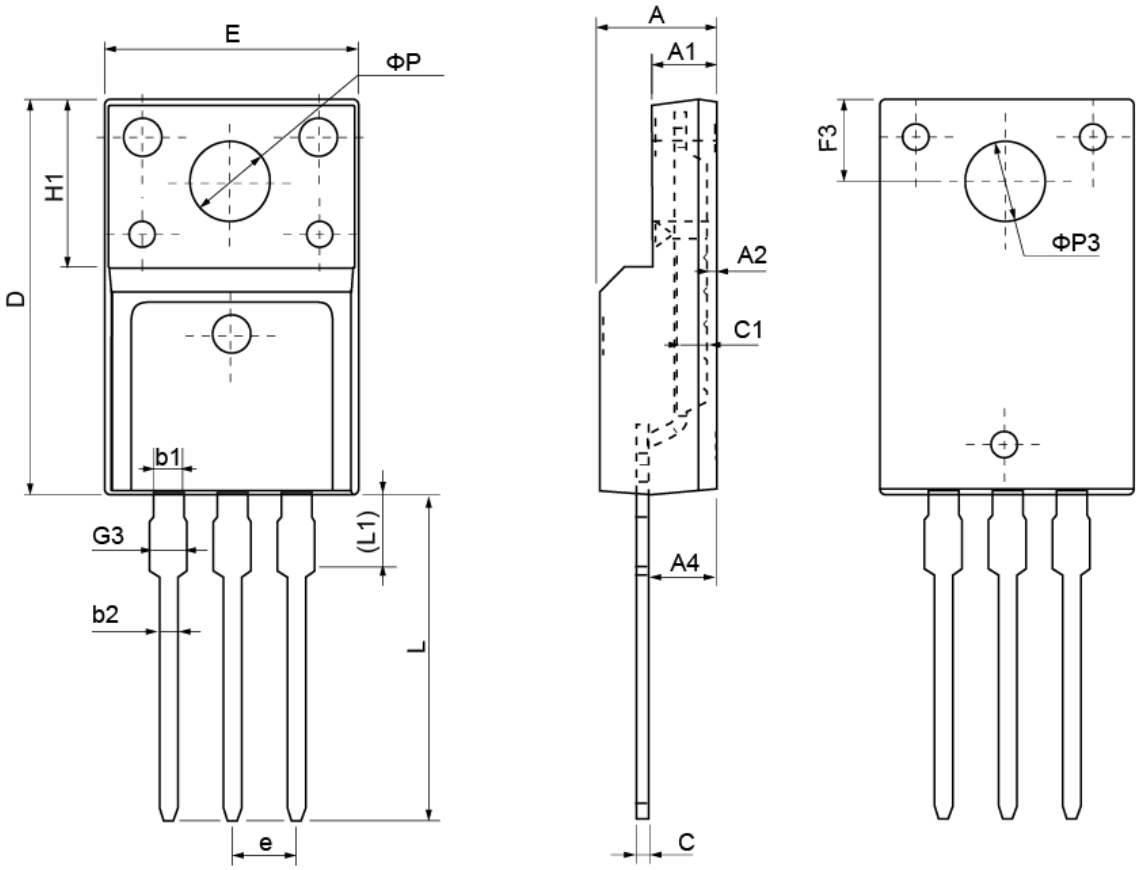
Figure 10. Transient Thermal Impedance TO-220/TO-263

TO-220 Package Outline Dimensions



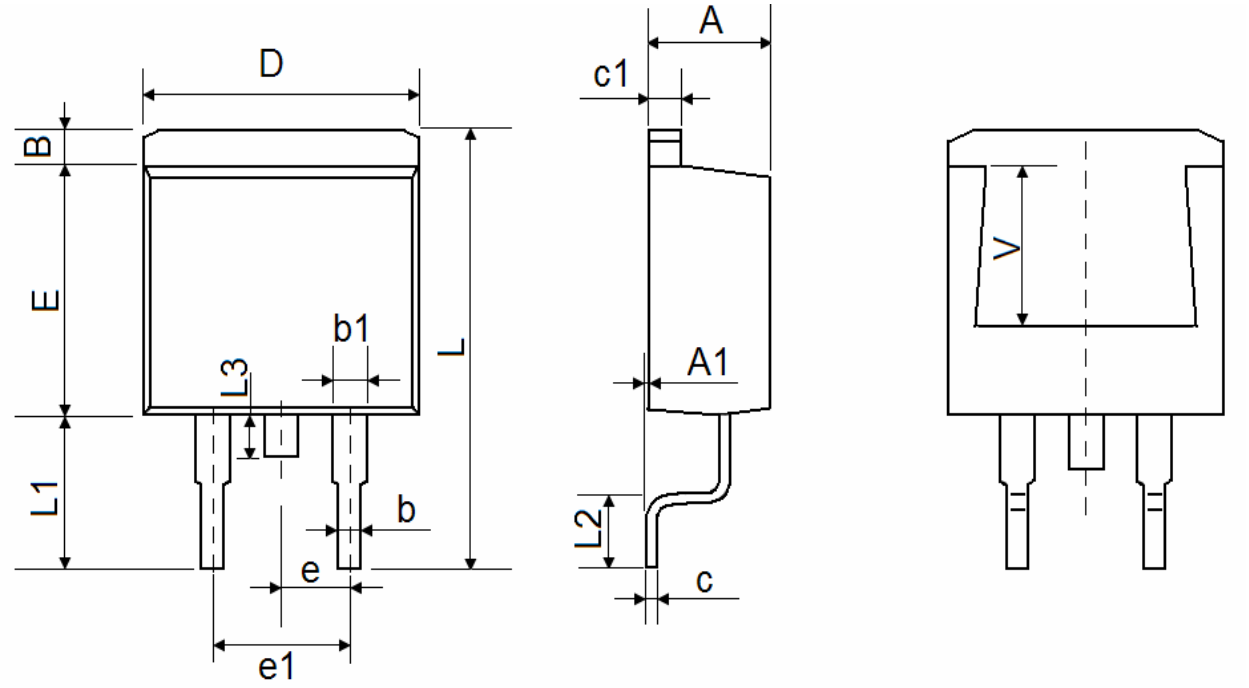
Symbol	Dimensions (unit:mm)			Symbol	Dimensions (unit:mm)		
	Min	Typ	Max		Min	Typ	Max
A	4.30	4.55	4.75	**E**	9.65	10.00	10.25
A1	1.15	1.30	1.45	**E3**	7.00	--	--
A2	2.20	2.40	2.60	**e**	2.54 BSC		
b	0.70	0.80	0.95	**e1**	5.08 BSC		
b2	1.17	1.27	1.47	**H1**	6.30	6.50	6.80
c	0.40	0.50	0.65	**L**	12.70	13.50	14.10
D	15.30	15.60	15.90	**L1**	--	3.20	3.95
D1	8.90	9.10	9.35	**ϕ P**	3.40	3.60	3.80
D2	5.50	--	--	**Q**	2.60	2.80	3.00

TO-220F Package Outline Dimensions



Symbol	Dimensions (unit:mm)			Symbol	Dimensions (unit:mm)		
	Min	Typ	Max		Min	Typ	Max
A	4.40	4.70	5.00	**H1**	6.70 REF		
A1	2.30	2.55	2.80	**L**	12.30	12.98	13.30
A2	0.30	0.50	0.70	**L1**	2.95	3.10	3.50
A4	2.45	2.80	3.05	**ϕP**	3.03	3.20	3.50
c	0.30	0.50	0.70	**ϕP3**	3.15	3.45	3.65
c1	1.20	1.30	1.40	**b1**	1.10	1.30	1.45
D	15.40	15.90	16.40	**b2**	0.60	0.80	1.00
E	9.86	10.16	10.46	**F3**	3.05	3.30	3.55
e	2.54 BSC			**G3**	1.15	1.35	1.55

TO-263 Package Outline Dimensions



Symbol	Dimensions (unit:mm)			Symbol	Dimensions (unit:mm)		
	Min	Typ	Max		Min	Typ	Max
A	4.40	4.55	4.70	**A1**	0.00	0.07	0.15
B	1.00	1.20	1.40	**b**	0.65	0.80	0.95
b1	1.10	1.15	1.37	**c**	0.30	0.40	0.53
c1	1.10	1.25	1.37	**D**	9.80	10.00	10.40
E	8.50	8.80	9.20	**e**	2.54 REF		
e1	4.90	5.10	5.40	**L**	14.80	15.20	15.70
L1	5.00	5.25	5.60	**L2**	2.05	2.45	2.80
L3	1.20	1.50	1.80	**V**	5.60 REF		

Printing Information

ATC ====Brand

XXXXXXX ====Material Code

XXYY ====XX Representative Year
YY Representative Weeks